

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes a substrate and an insulating layer formed on the substrate. A first device may be formed on the insulating layer. The first device may include a first fin formed on the insulating layer, a first dielectric layer formed on the first fin, and a partially silicided gate formed over a portion of the first fin and the first dielectric layer. A second device also may be formed on the insulating layer. The second device may include a second fin formed on the insulating layer, a second dielectric layer formed on the second fin, and a fully silicided gate formed over a portion of the second fin and the second dielectric layer.